

R-C Thermal Model Parameters

DESCRIPTION

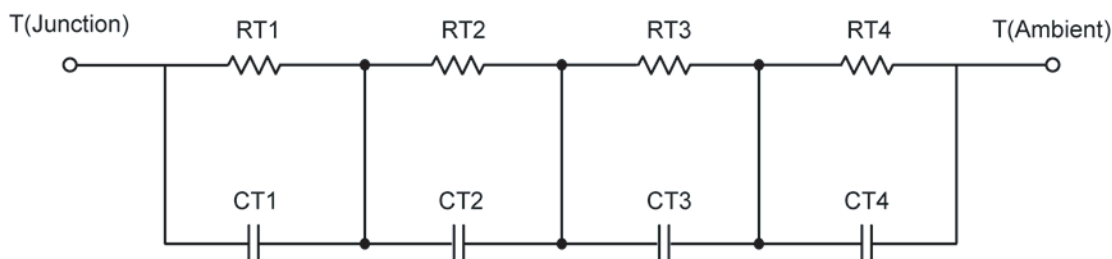
The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION			
Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RT1	21.9604	N/A	5.7953
RT2	6.3818	N/A	923.7476 m
RT3	13.3371	N/A	5.8236
RT4	37.9264	N/A	8.4613
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CT1	41.6847 m	N/A	54.8120 m
CT2	8.8410 m	N/A	1.2546 m
CT3	356.1870 m	N/A	12.8310 m
CT4	2.0833	N/A	196.0715 m

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance (°C/W)			
Junction to	Ambient	Case	Foot
RF1	5.1205	N/A	1.6149
RF2	23.7400	N/A	8.9202
RF3	14.9587	N/A	7.2244
RF4	35.7281	N/A	3.2532
Thermal Capacitance (Joules/°C)			
Junction to	Ambient	Case	Foot
CF1	4.8970 m	N/A	1.9824 m
CF2	21.5550 m	N/A	8.7635 m
CF3	162.1276 m	N/A	68.3828 m
CF4	1.9274	N/A	473.3334 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002

